

20V N-Channel MOSFET

Product Summary

| V(BR)DSS | R _{DS(on)MAX} | l _D |
|----------|------------------------|----------------|
| | 32mΩ@4.5V | |
| 20V | 40mΩ@2.5V | 4.5A |
| | 70mΩ@1.8V | |

Feature

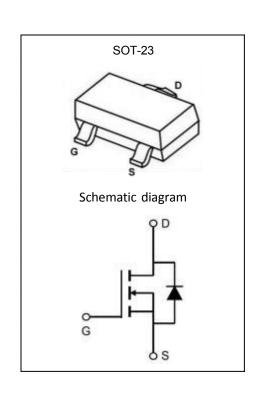
- TrenchFET Power MOSFET
- Excellent R_{DS(on)} and Low Gate Charge

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:





ABSOLUTE MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|------------------|-----------|------------|
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | Vgs | ±12 | V |
| Continuous Drain Current | I _D | 4.5 | A |
| Pulsed Drain Current ⁽¹⁾ | I _{DM} | 18 | A |
| Power Dissipation | P _D | 0.35 | W |
| Thermal Resistance from Junction to Ambient ⁽²⁾ | Rеja | 357 | °C/W |
| Junction Temperature | TJ | 150 | $^{\circ}$ |
| Storage Temperature | T _{STG} | -55~ +150 | $^{\circ}$ |



MOSFET ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Туре | Max | Unit |
|--|---------------------|---|------|------|------|---------------------|
| STATIC CHARACTERISTICS | | | | • | | |
| Drain-source breakdown voltage | V(BR)DSS | V _{GS} = 0V, I _D =250μA | 20 | | | V |
| Zero gate voltage drain current | I _{DSS} | V _{DS} =20V,V _{GS} = 0V | | | 1 | μA |
| Gate-body leakage current | Igss | V _{GS} =±12V, V _{DS} = 0V | | | ±100 | nА |
| Gate threshold voltage(3) | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 0.45 | 0.7 | 1 | V |
| | | Vgs =4.5V, ID =3A | | 21 | 32 | |
| Drain-source on-resistance(3) | R _{DS(on)} | Vgs =2.5V, ID =2A | | 27 | 40 | $_{\text{m}}\Omega$ |
| | | Vgs =1.8V, ID =2A | | 44 | 70 | |
| Forward tranconductance ⁽³⁾ | grs | V _{DS} =10V, I _D =6A | | 5 | | S |
| DYNAMIC CHARACTERISTICS(4) | | | | | | |
| Input Capacitance | Ciss | | | 523 | | |
| Output Capacitance | Coss | V _{DS} =8V,V _{GS} =0V,f=1MHz | | 99 | | pF |
| Reverse Transfer Capacitance | Crss | | | 75 | | |
| SWITCHING CHARACTERISTICS(4) | | | | | | |
| Turn-on delay time | t _{d(on)} | | | 10.5 | 21 | |
| Turn-on rise time | t _r | V _{GS} =4.5V,V _{DS} =10V, | | 4.5 | 9 | |
| Turn-off delay time | t _{d(off)} | I _D =1A,R _{GEN} =6Ω | | 27.5 | 55 | ns |
| Turn-off fall time | t _f | | | 4.3 | 8.6 | |
| Total gate charge | Qg | | | 6.4 | 8.2 | |
| Gate-source charge | Qgs | V _{DS} =10V,V _{GS} =4.5V,I _D =6A | | 1.8 | 2.3 | nC |
| Gate-drain charge | Qgd | | | 1.3 | 1.9 | |
| SOURCE-DRAIN DIODE CHARACTERIS | TICS | | | | | |
| Body Diode Voltage ⁽³⁾ | V _{SD} | Is=1.7A, V _{GS} = 0V | | 0.8 | 1.2 | V |
| Continuous Source-Drain Diode Current | Is | Tc=25℃ | | | 1.7 | Α |

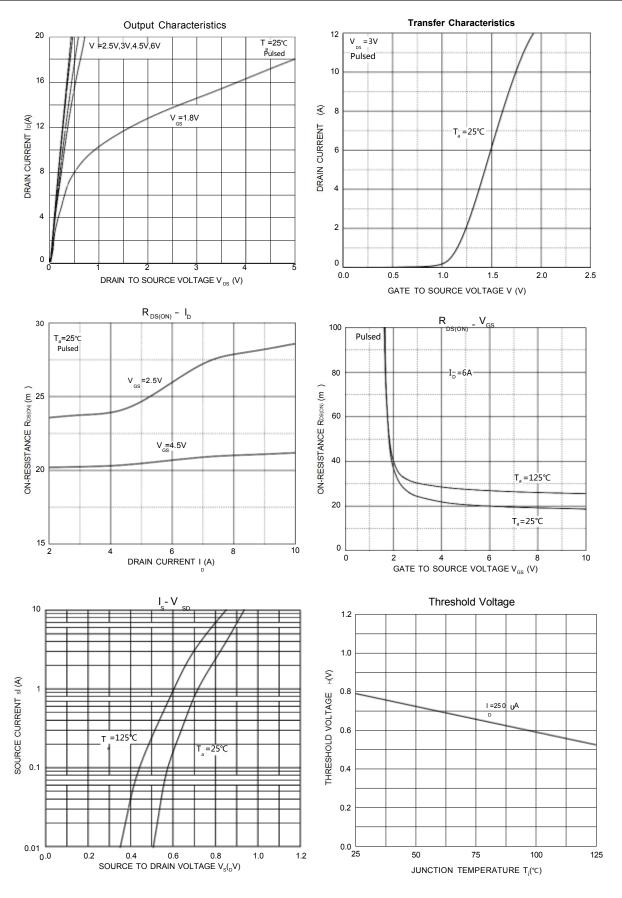
Notes:

- 1. Repetitive rating: Pulse width limited by junction temperature.
- 2. Surface mounted on FR4 board , t≤10s.
- 3. Pulse Test : Pulse Width≤80µs, Duty Cycle≤0.5%.
- 4. Guaranteed by design, not subject to producting.

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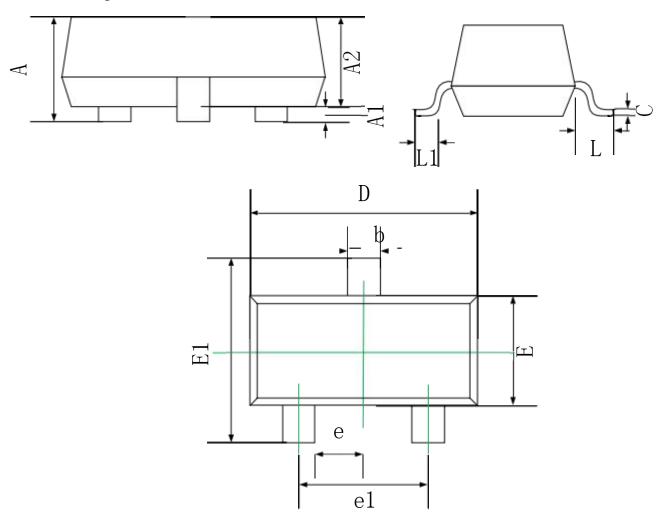


Typical Electrical and Thermal Characteristics





SOT-23 Package Information

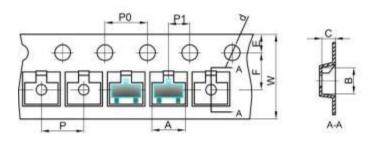


| Symbol | Dimensions In Millimeters | | | | | |
|--------|---------------------------|------|--|--|--|--|
| Symbol | Min. | Max. | | | | |
| Α | 0.90 | 1.15 | | | | |
| A1 | 0.00 | 0.10 | | | | |
| A2 | 0.90 | 1.05 | | | | |
| b | 0.30 | 0.50 | | | | |
| С | 0.08 0.15 | | | | | |
| D | 2.80 3.00 | | | | | |
| E | 1.20 | 1.40 | | | | |
| E1 | 2.25 | 2.55 | | | | |
| е | 0.95 REF. | | | | | |
| e1 | 1.80 2.00 | | | | | |
| L | 0.55 | REF. | | | | |
| L1 | 0.30 | 0.50 | | | | |

SOT-23 Tape and Reel

SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

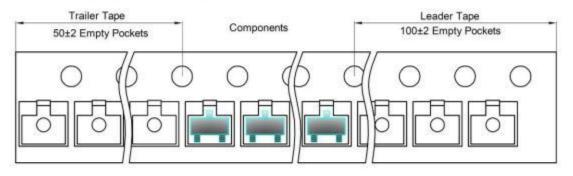


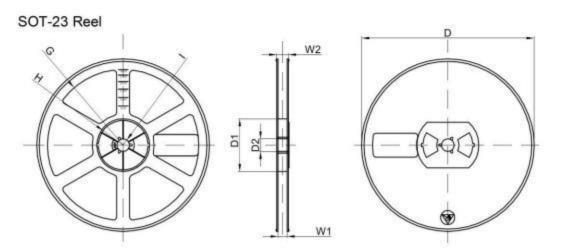
Packaging Description:

SOT-23 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7° or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|------|------|------|-------|------|------|------|------|------|------|
| Pkg type | A | В | С | d | Ε | F | P0 | Р | P1 | W |
| SOT-23 | 3.15 | 2.77 | 1.22 | Ø1.50 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |

SOT-23 Tape Leader and Trailer





| | | | Dimension | ons are in millime | ter | | | |
|-------------|---------|-------|-----------|--------------------|--------|-------|------|-------|
| Reel Option | D | D1 | D2 | G | н | 1 | W1 | W2 |
| 7"Dia | Ø178.00 | 54.40 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 12.30 |

| REEL | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) | G.W.(kg) |
|----------|-----------|------------|--------------|-------------|-----------------|----------|
| 3000 pcs | 7 inch | 30,000 pcs | 203×203×195 | 120,000 pcs | 438×438×220 | |

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